

Status of parasitic FE from metallic surfaces and potential destruction of emitters by μ -discharges and ion beam impact

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- Motivation
- Measurement techniques & samples
- Field emission results before and after cleaning
- Destruction of emitters by μ -discharges
- First results on Ar ion bombardment
- Conclusions and outlook

Motivation

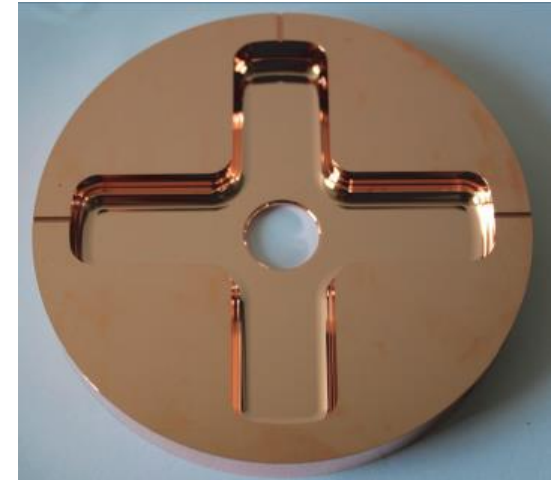
- Field emission (FE) creates “dark current” which absorbs rf energy, causes radiation, it seems to be the precursor of electric breakdown (BD);
- In turn, BD limits the operation of accelerators and can cause irreversible damage to their physical structure;
- The acceleration gradient for the present CLIC design is $E_{\text{acc}}=100$ MV/m ($E_{\text{peak}}=243$ MV/m) and achievable only after long conditioning of the structures [2];
- Deep and quantitative understanding of the origin of BD processes is important;

Goal: suppression of BD by using proper surface treatments.

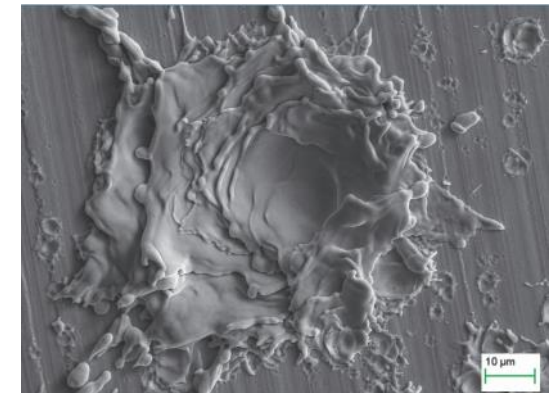
Task: investigation of FE from flat Cu surfaces

- What causes FE from (relevant) Cu samples?
- How to reduce/avoid FE?

BMBF project 05H12PX6



Cu disc of CLIC accel. structure [1]



Surface damage due to breakdown [1]

[1] A.T. Perez & G. Arnau, “Determination of dislocations density in Cu-OFE for CLIC project by using EBSD”, Poster, MeVArc 2013

[2] W. Wuensch, “Study of the conditioning of RF structures”, Presentation, MeVArc 2015.

Surface quality control

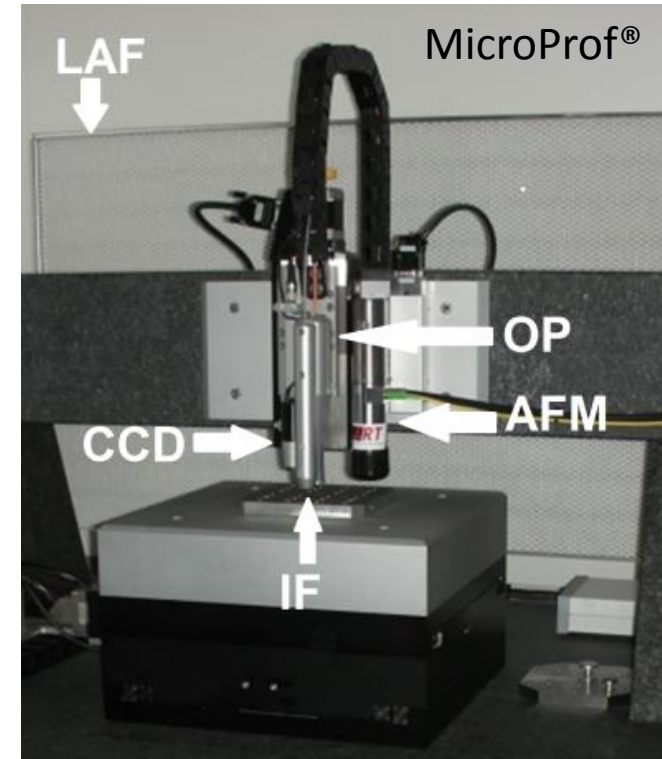
○ Optical Profilometer (OP)

- white light irradiation and spectral reflection (chromatic aberration)
- 20x20 cm² scanning range in 2 cm distance
- Curved surface up to 5 cm height difference
- 2 μm (3 nm) lateral (height) resolution

○ Further zooming by AFM:

- ±2 μm positioning relative to OP results
- 98x98 μm² scanning range
- 3 (1) nm lateral (height) resolution
- contact or non-contact modes.

- Clean laminar air flow (LAF) from the back
- Granite plate with active damping system
- CCD camera for fast positioning
- interferometric film thickness sensor (IF)

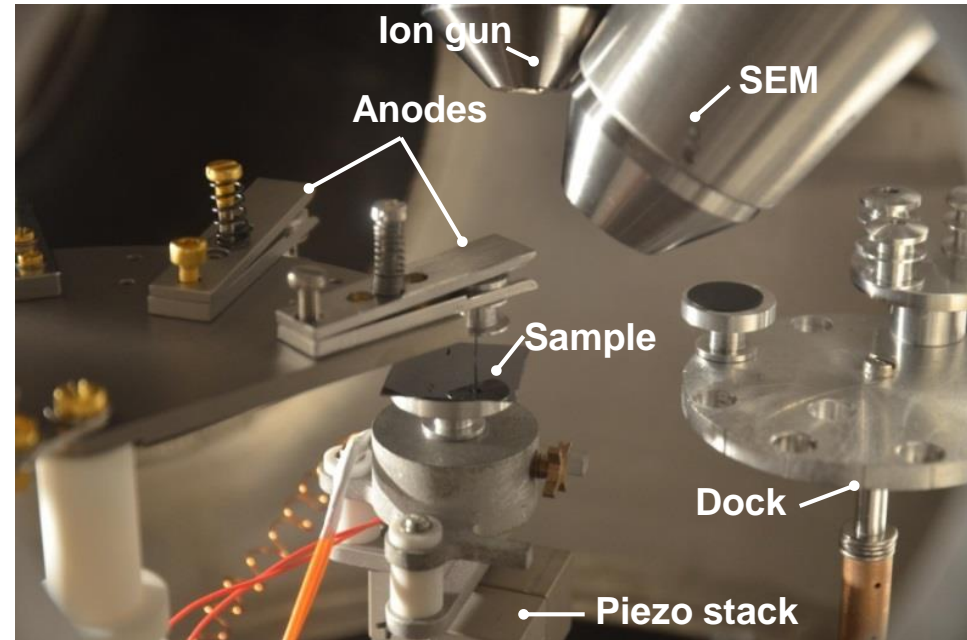
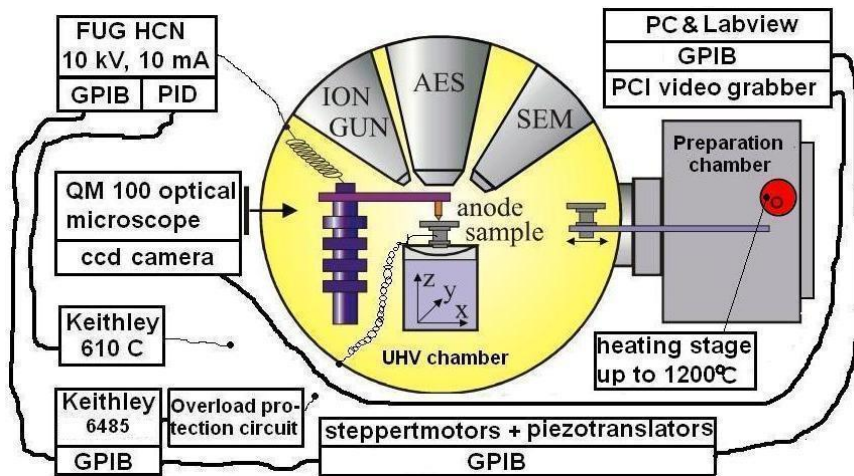


www.frt-gmbh.com

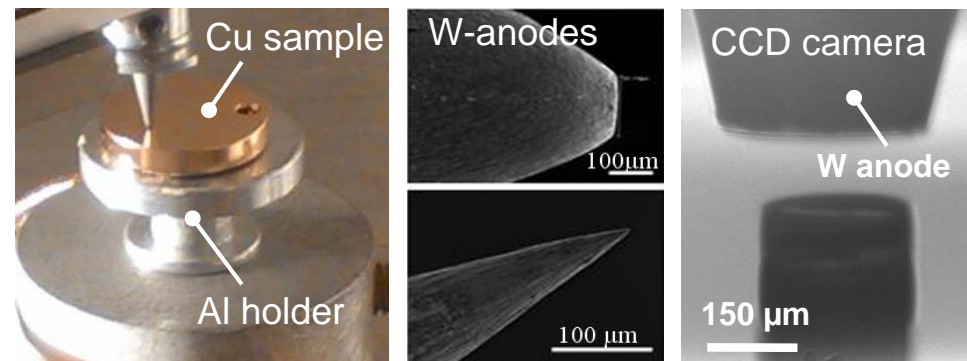
DC field emission scanning microscope (FESM)

Provides PID-regulated **voltage scans** $V(x,y)$ @ fixed current (typ. $I=1\text{nA}$): $E_{\text{act}} (1\text{nA})$

- **activation**, **localization** and **number density N** of emitters
- **local** $U(z)$ and $I(V)$ measurements of single emitters: $E_{\text{on}}(1\text{nA})$, β_{FN} , S_{FN}



- base UHV at 10^{-7} Pa
- exchangeable W-anodes $3\text{...}330\ \mu\text{m}$
- cathodes up to $25 \times 25\ \text{mm}^2$
- 3D drives: stepper motor/piezo-translator ($100/40\ \text{nm/step}$)
- cathode tilt correction: $\pm 1\ \mu\text{m}$ within $\pm 5\ \text{mm}$
- gap monitored via CCD camera ($1\ \mu\text{m}$ resolut.)
- heat treatments ($< 1200^\circ\ \text{C}$)
- auger electron spectroscopy (AES): chemical state
- ion gun: for local emitter cleaning
- ex-situ SEM & EDX: identification of emitting defects
- clean laminar air flow around load-lock



D. Lysenkov, G. Müller, *Int. J. of Nanotechnology* 2, 2005.

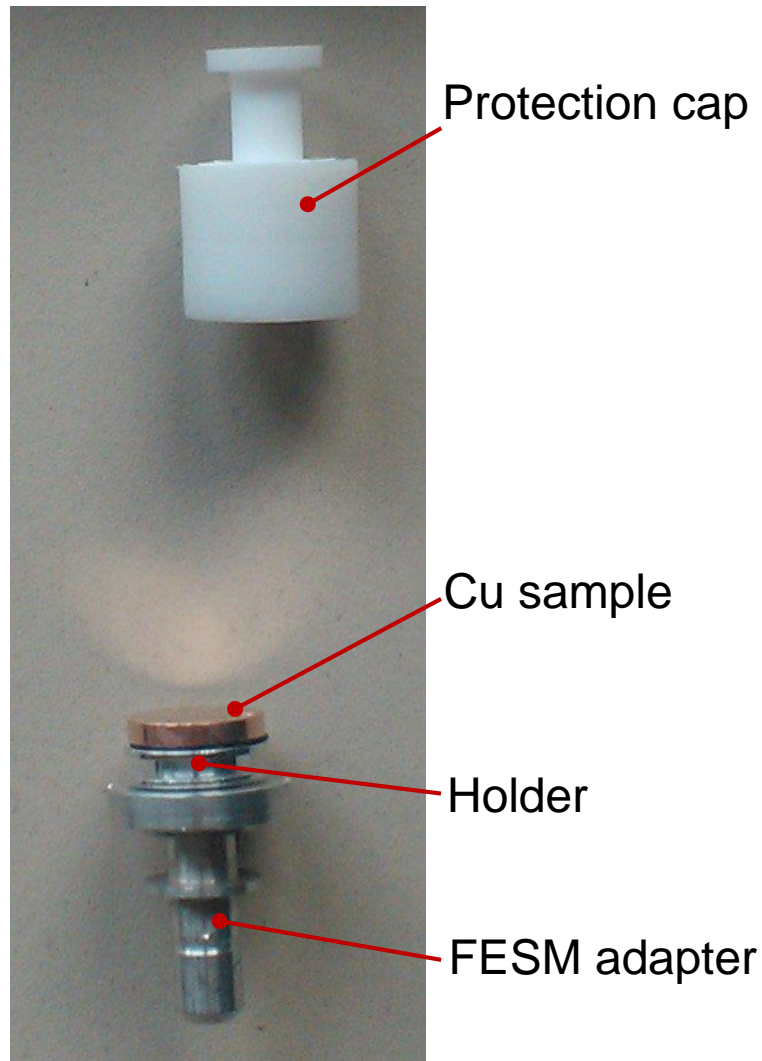
Samples

Fabrication at CERN:

- Flat polycrystalline **Cu** samples of $\varnothing = 11$ mm
- Small hole (0.5mm) as mark to identify the emitter position in different systems (SEM/FESM)
- Diamond turned (**DT**) samples
- Additional chemical etching (**SLAC** treatment: using H_3PO_4 , HNO_3 , acetic glacial acid and HCl , to remove a surface layer of $0.6 \mu\text{m}$)

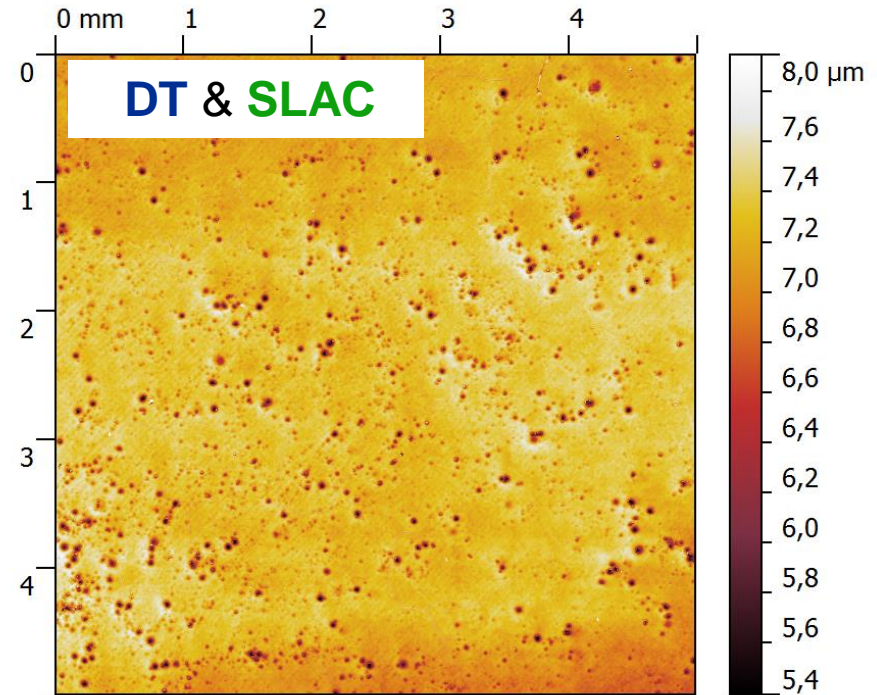
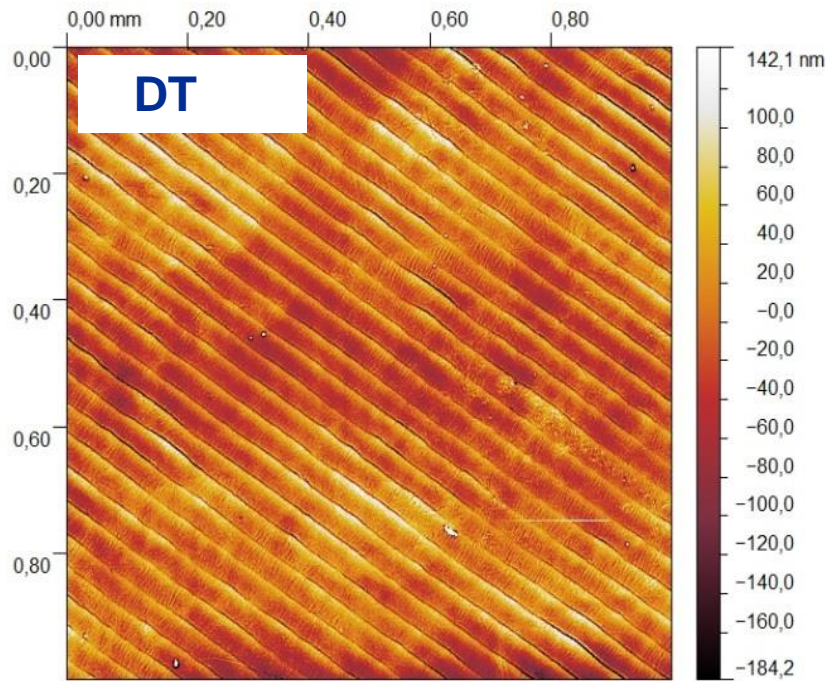
Investigation at BUW:

- Transport under Teflon® protection cap to avoid any surface damage and contaminations after polishing and cleaning
- Glued with SEM button on Al holder and mounted to an adapter for the FESM
- Caps opened under HV or clean room (ISO5)
- Final **cleaning** (N_2 , DIC)
- **OP+AFM/FESM/SEM+EDX** measurements



Surface quality

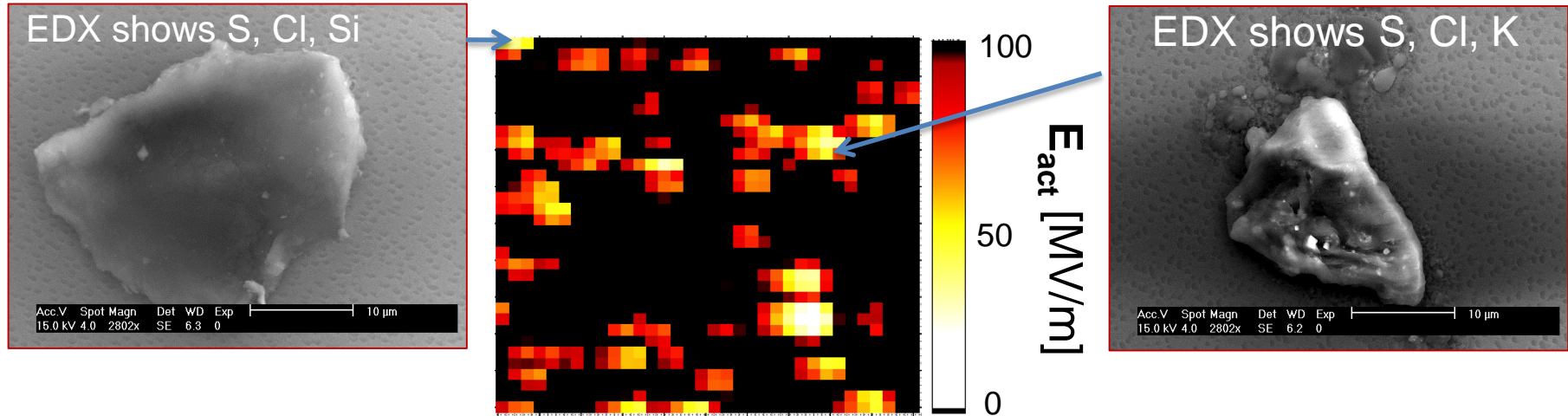
Samples measured with optical profilometer (OP) in the area relevant for FESM



- Slightly wavy surface ($\lambda \sim 0,5 - 1$ mm)
- Many ridges from DT
- Damage layer?
- Average roughness: $R_a/R_q = 126/145$ nm
- Sample surface now very flat ($\pm 0,5$ μm)
- Many pits ($N < 18$ mm⁻²) due to etching
- Grain size: 1300 μm² - 5.3 mm²
- $R_a/R_q = 150/230$ nm slightly increased

FESM/SEM/EDX results

E-map for the sample DT+SLAC #1 before cleaning (1 nA, area 5x5 mm²)



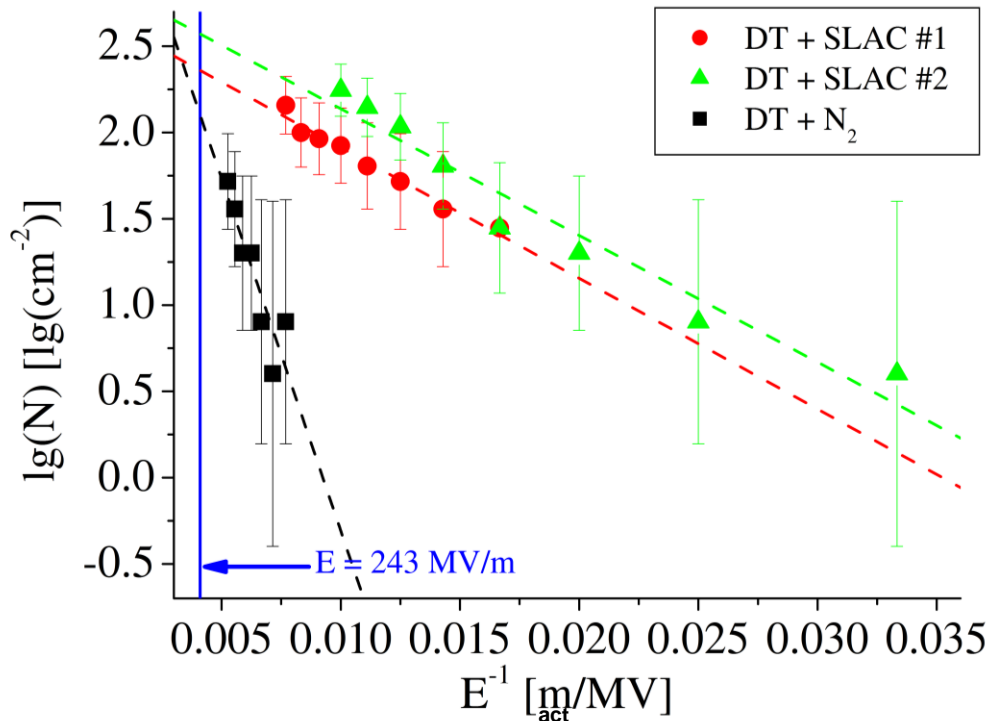
SEM/EDX analysis of Cu surface:

- 60% particulates (Al, Cl, S, Si, K)
- 10% surface defects
- 30% emission sites: unknown origin

• EFE is dominated by foreign particulates: cleaning the surface to reduce FE

FE activation statistics without/with N₂ cleaning

for two types of samples



- Emission from surfaces **without** any **cleaning** starts at **30 MV/m**
- **Cleaning** with N₂ shows FE starting at **130 MV/m**
- N @ $E_{\text{peak}} = 243 \text{ MV}/\text{m}$ reduces from **229/372** cm^{-2} to **124** cm^{-2}
- N increases exponentially [3]:
$$N \sim \exp(1/E_{\text{act}})$$

[3] S. Lagotzky, G. Müller, submitted to Nucl. Instr. Methods Phys. Res. Sect. A (2015).

Dry ice cleaning (DIC) system

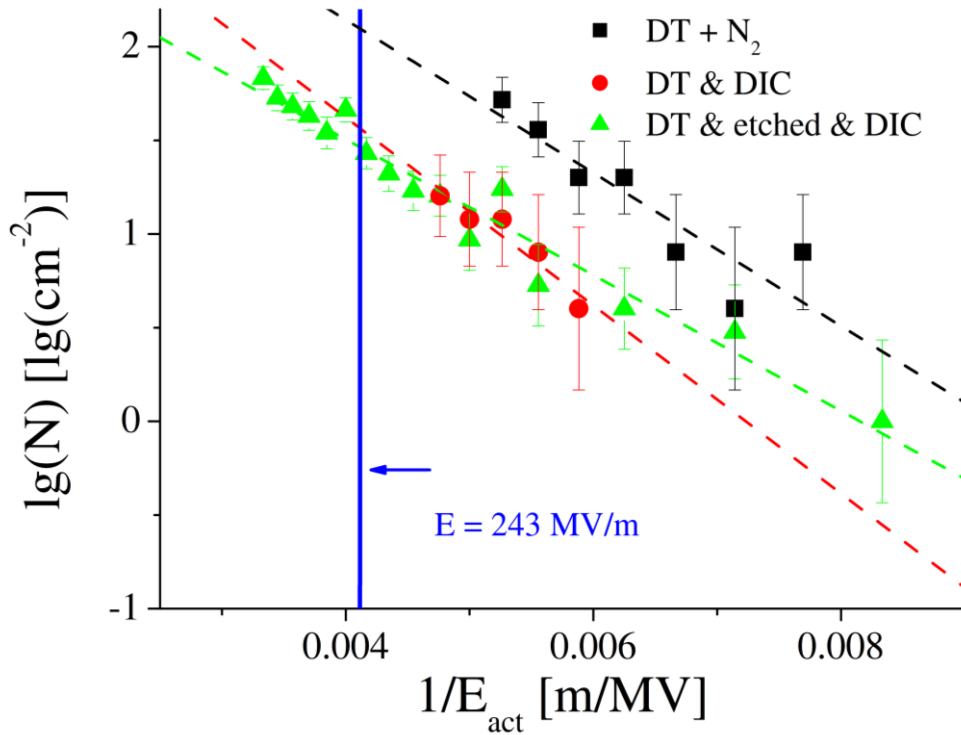


- Commercial DIC system (SJ-10, CryoSnow) installed in cleanroom (class iso 5)
- Non-abrasive blasting where dry ice is accelerated in a pressurized air stream and directed at the surface
- Samples/caps cleaned for 2.5 min under 90° /45° and 3 x rotated in 90° steps
- Most particulates (> 100 nm) are removed

www.cryosnow.com

FE activation statistics after DIC cleaning

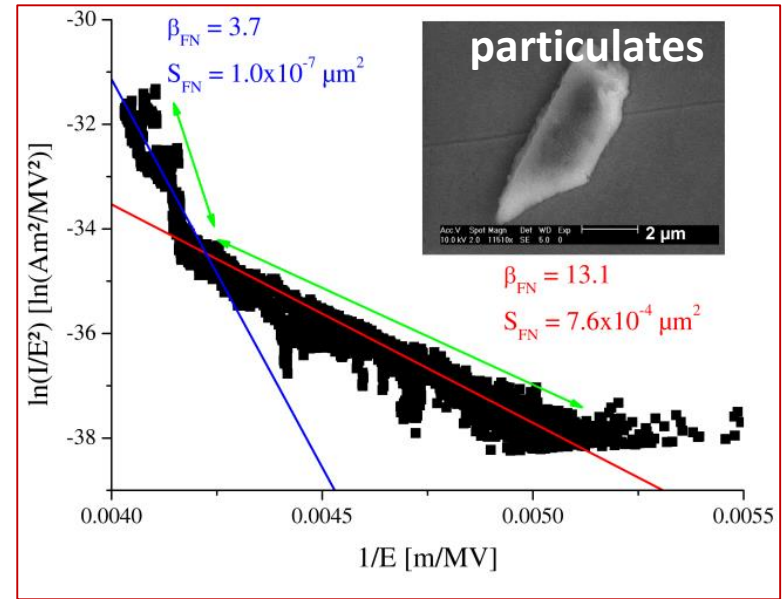
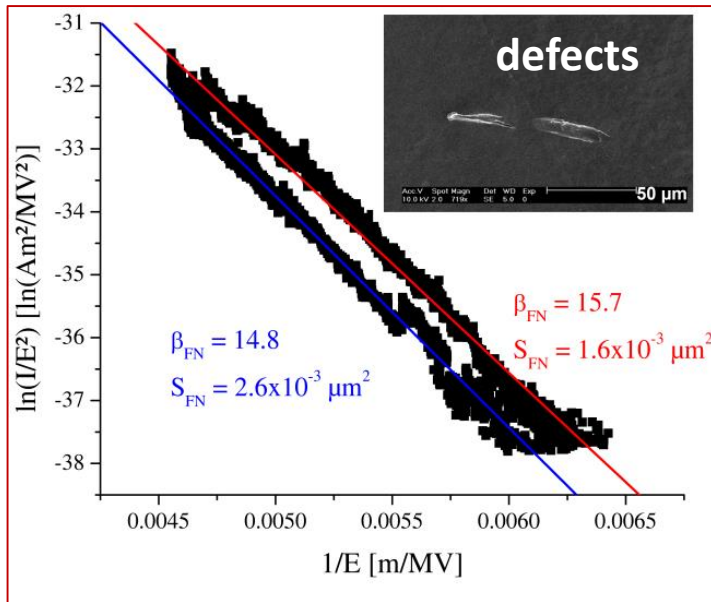
for three types of samples



- DIC reduces N significantly
- N @ $E_{\text{peak}} = 243 \text{ MV/m}$ reduces from 124 cm^{-2} to 29 cm^{-2}
- Chemical etching didn't reduce N

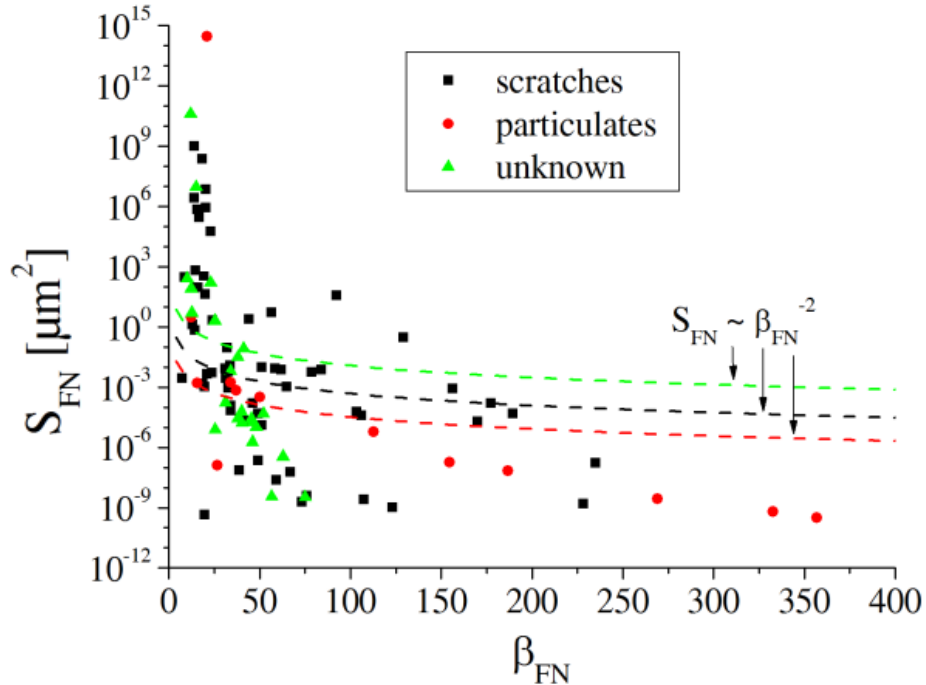
Single emitter characteristics on DIC-cleaned samples

SEM/EDX : 57% surface defects; 12% particulates (Al, Si, W); 31% unidentified;



- Rather stable FE
- Slight jumps probably due to melting of micro-tips
- More unstable FE
- Changed slope at high fields due to bad electrical contact to bulk

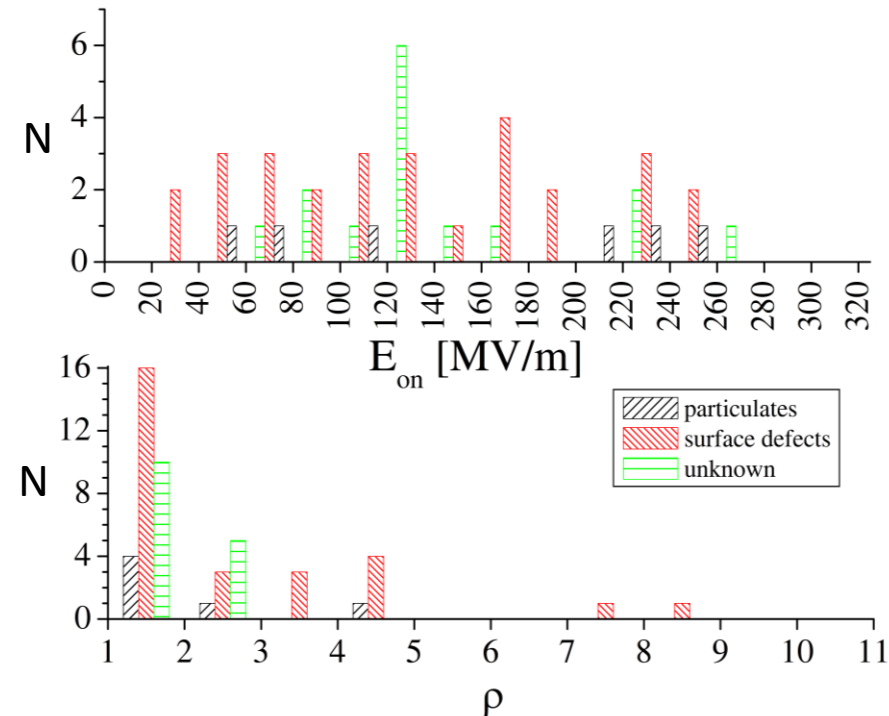
Correlation between S_{FN} and β_{FN}



- Highest β_{FN} are caused by particulates
- Most S_{FN} and β_{FN} are in a reasonable range for all types of emitters
- Most data are correlated: $S_{FN} \sim \beta_{FN}^{-2}$
- No correlation at low β_{FN} : high S_{FN} values with respect to the anode size hint at other FE mechanisms like MIV- and MIM-emission [4]

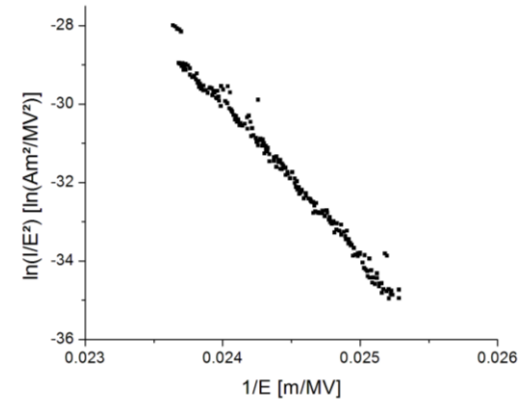
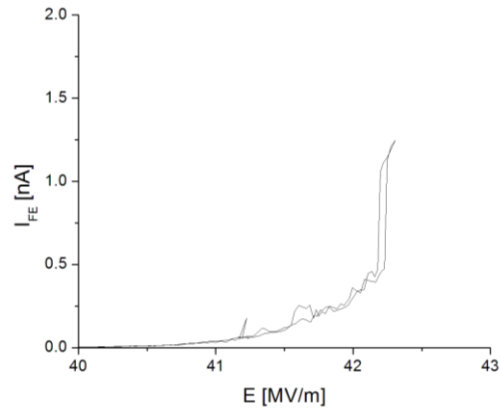
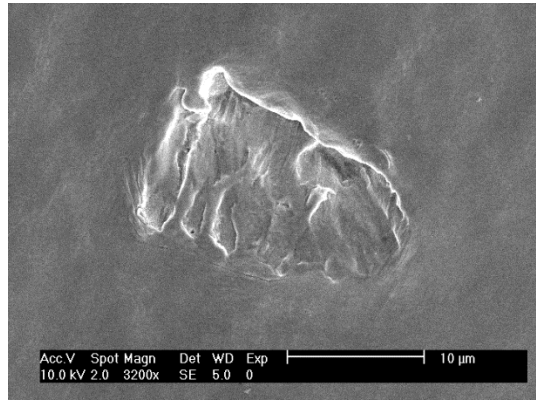
[4] R. V. Latham, High voltage vacuum insulation, Academic Press, London (1995).

Possible origin of breakdowns in FR structures

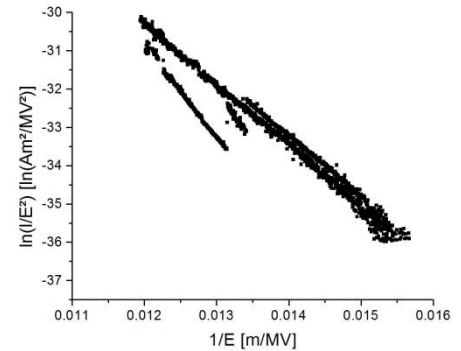
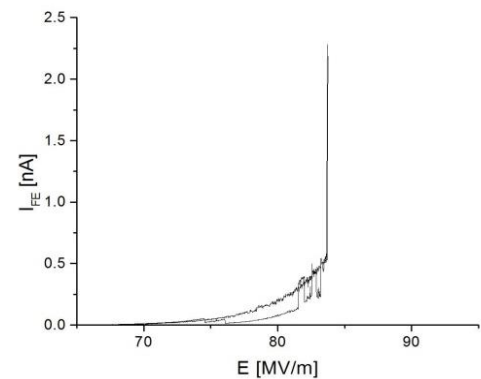
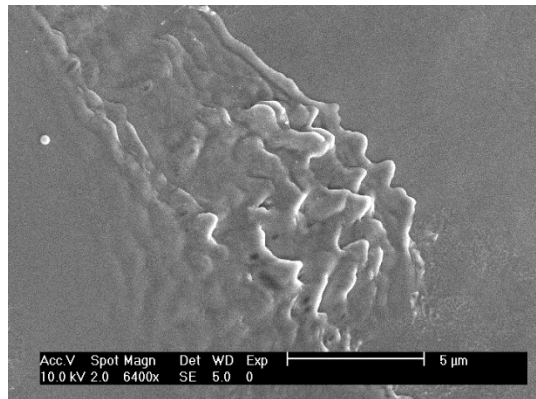


- All emitters yielded a reduced $E_{on} < E_{act}$ hence, emitters can lead to strong e^- loading of accelerating structures if activated
- **Activation strength** described by field reduction function $\rho = E_{act}/E_{on}$
- 20% of emitters show $\rho > 3$ (surface defects)
- High- ρ emitters would cause an emitter explosion and a BD of the cavity field

Examples: two candidates for breakdowns



- Activated between $E_{act} = 240-250$ MV/m, $E_{on} = 54$ MV/m $\rightarrow \rho = 4.62$
 \rightarrow calculated current @ 243 MV/m: $I_{FN} \sim 10^{22}$ A!



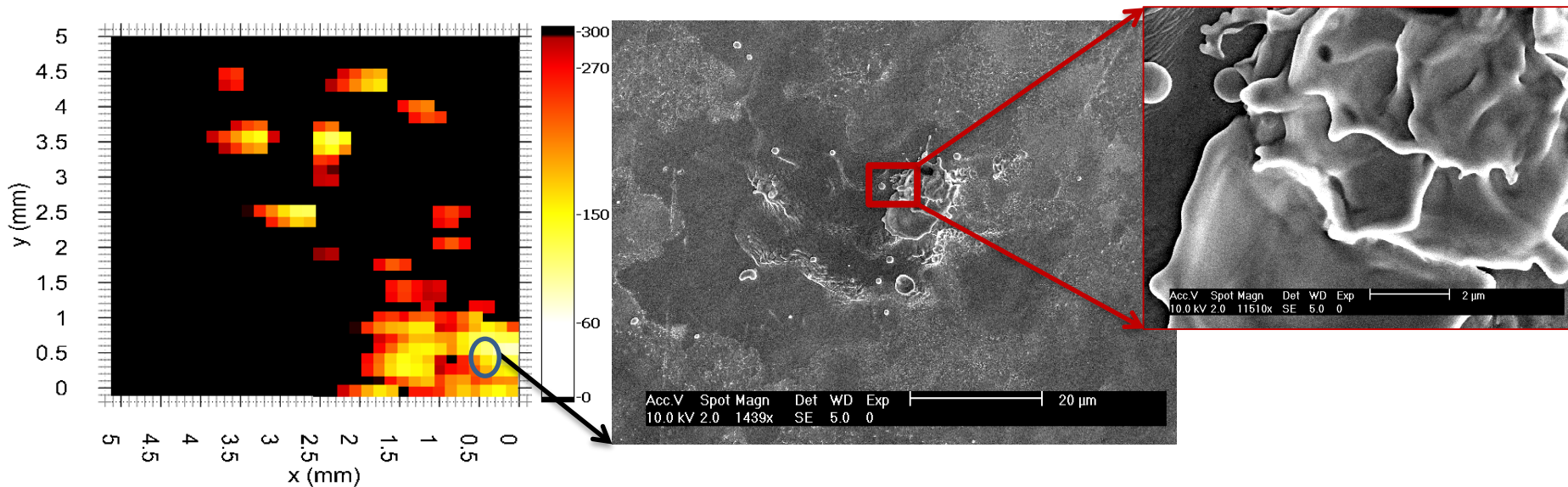
- Activated between $E_{act} = 130-140$ MV/m, $E_{on} = 80$ MV/m $\rightarrow \rho = 1.75$
 \rightarrow calculated current @ 243 MV/m: $I_{FN} \sim 3$ mA

Accidental discharges in the FESM on Cu

Usually discharges are prevented **during FESM scans** by the PID voltage regulation

Nevertheless, some **unwanted discharges** happen:

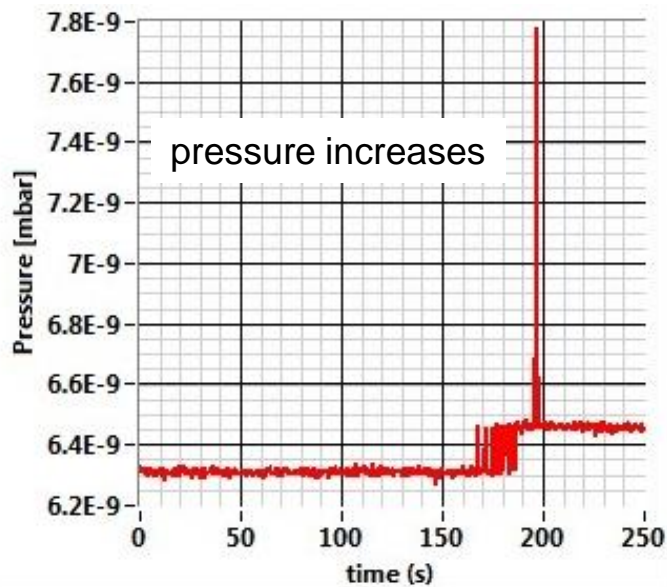
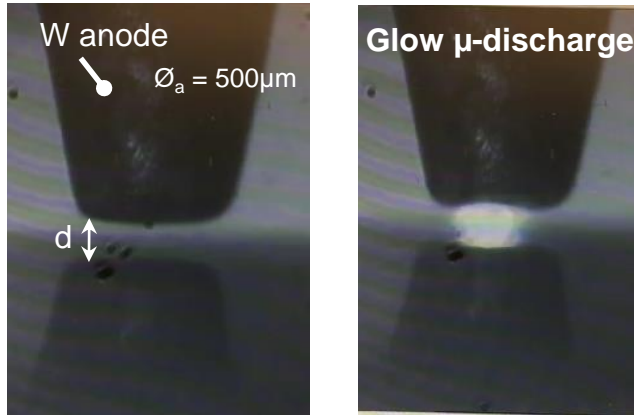
- during scans (if the current jump is faster than ~ 2 ms)
- during local measurements (because of activation effects)



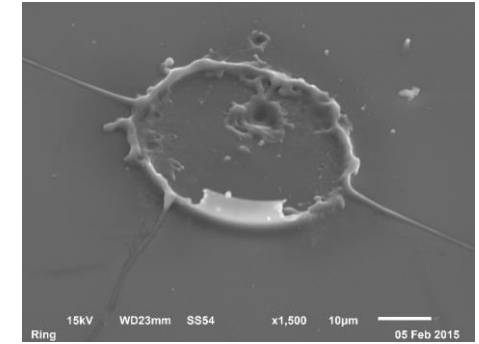
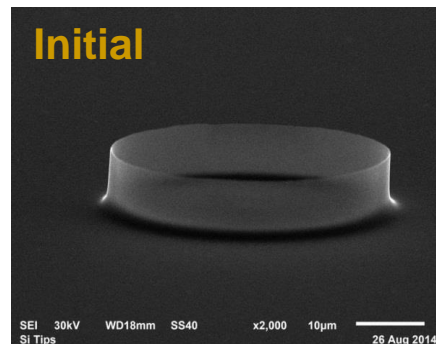
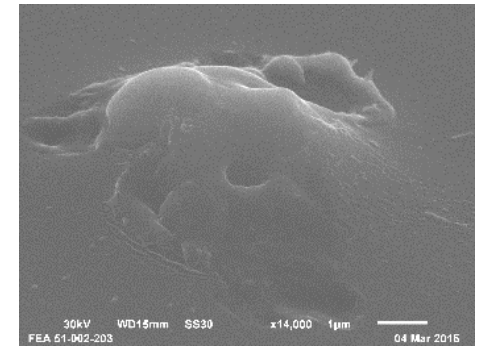
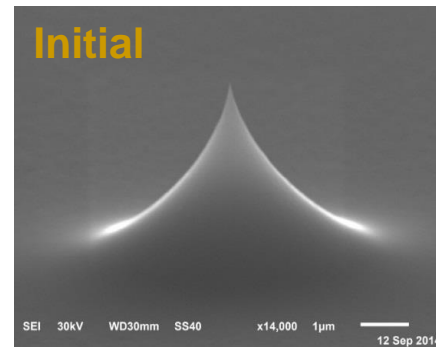
- **Discharges** (most-likely caused by high-p emitters) **destroy the surface** and lead to the **formation of new stable** and **strong emitters**, probably similar to BDs in cavities
- In accelerating structures such a new emitter triggers the next BD, which forms another emitter, that ignite a BD etc.

μ -discharges in the FESM on Si samples

CCD camera images of vacuum gap and glow μ -discharge



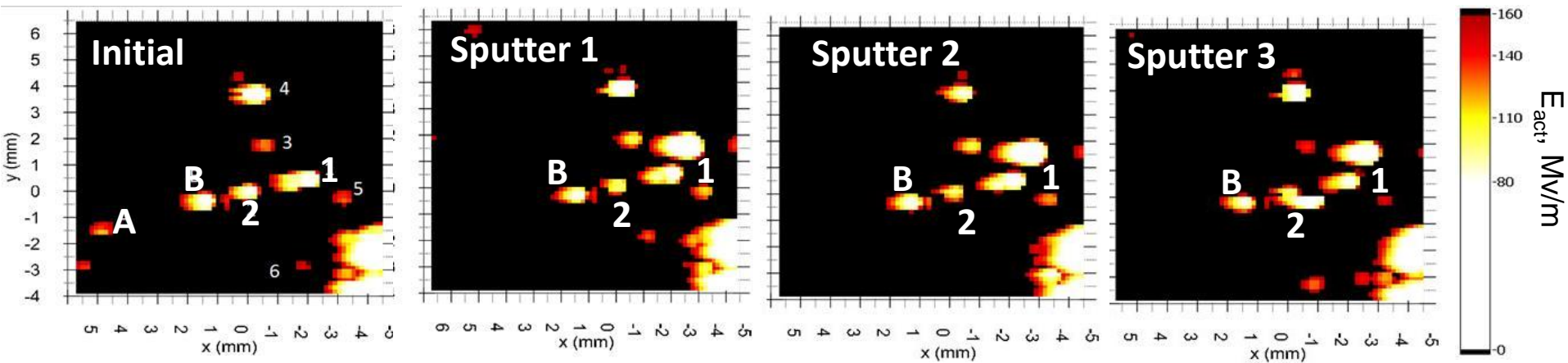
SEM images of different emitters before/after



Discharges lead to

- morphological changes (significantly shortened, partially/completely removed emitters)
- create craters;

First results on Ar ion bombardment (local sputtering) of Nb



- Emitter **A** was **deactivated**;
- Emitters become **weaker** even at moderate ion energy (max. 2keV);
- **Formation** of new emitters?

Emitter No.	initial	Sputter 1 $E_{ion} = 1\text{keV}$, $t=1\text{h}$	Sputter 2 $E_{ion} = 1\text{keV}$, $t=1\text{h}$	Sputter 3 $E_{ion} = 2\text{keV}$, $t=1\text{h}$
	β_{FN}	β_{FN}	β_{FN}	β_{FN}
A	not meas.	gone	-	-
B	100	100	57	69
1	114	85	85	85
2	58	58	47	32

Conclusions & outlook

- Actual surface quality of DT+SLAC etched Cu not sufficient for CLIC structures
 - $N = 229 \text{ \& } 370 \text{ cm}^{-2}$ at $E = 243 \text{ MV/m}$, mainly caused by particulates
- **Cleaning with N_2 (DIC) decreases N significantly by a factor $\sim 1.8\text{-}2.8$ (7.7-12.3)**
 - $N = 124 \text{ (29) cm}^{-2}$ at $E = 243 \text{ MV/m}$, mainly caused by surface defects
- **Geometrical field enhancement not sufficient to explain FE of Cu surfaces**
 - Alternative emission processes like the MIV/MIM-model or field-induced protrusion growth
 - Activated emitters with high ρ are candidates for BDs in accelerating structures
- μ -discharges destroy emitters but often create new emitters/craters
- **Low energy Ar ion bombardment is more reliable way to weaken/remove emitters**
- Current and ion conditioning of emitters on Nb will be studied in the next project

Acknowledgements:

Funding by BMBF projects 05H12PX6 (completed) and 05H15PXR1 (just started)



Thank you for your attention

5th International Workshop on Mechanisms of Vacuum Arcs, 1-5 September 2015



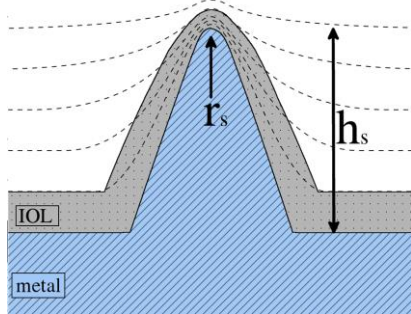
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Activation of emitters

- Insulating oxide layer (IOL, thickness $d_{ox} \sim \text{few nm}$) on metallic surfaces
- Question: How are emitters activated?

Surface defects (MIV)

$$\beta_{MIV}^{act} \approx h_s / r_s$$

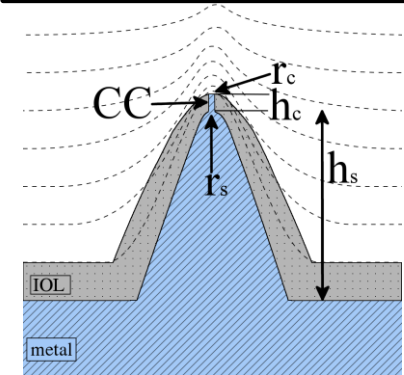


Conducting channel (CC) is burned into oxide by activated emission current

always stronger

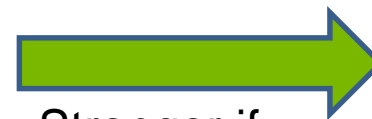
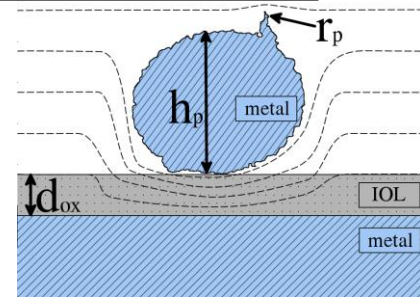


$$\beta_S^{on} \approx h_s / r_s \cdot (h_c / r_c)$$



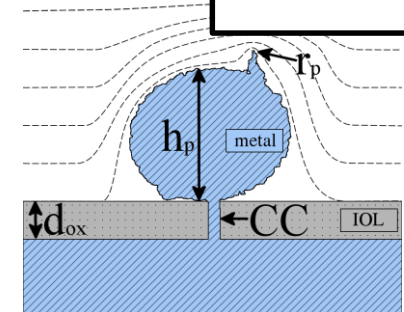
Particulates (MIM)

$$\beta_{MIM}^{act} \approx h_p / d_{ox}$$



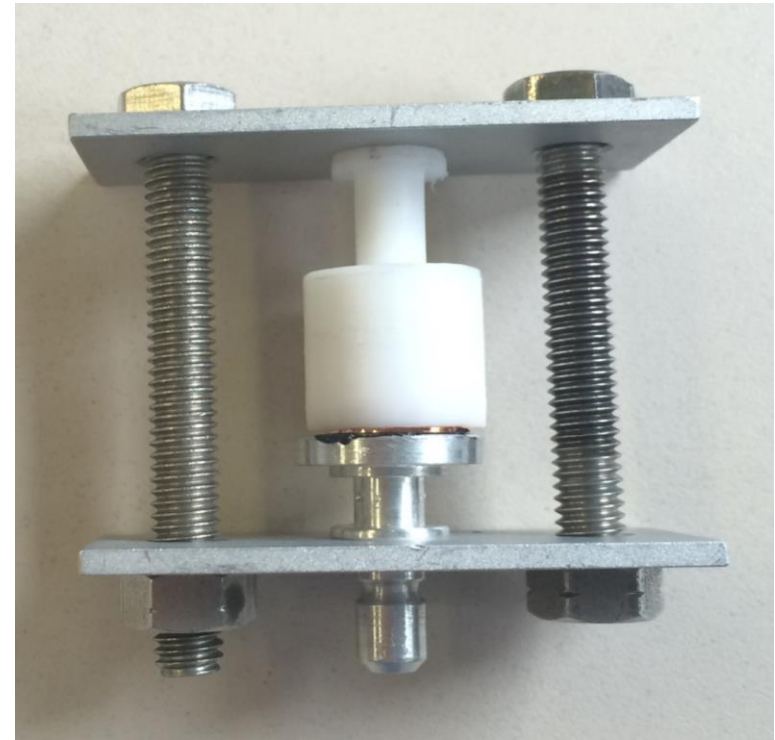
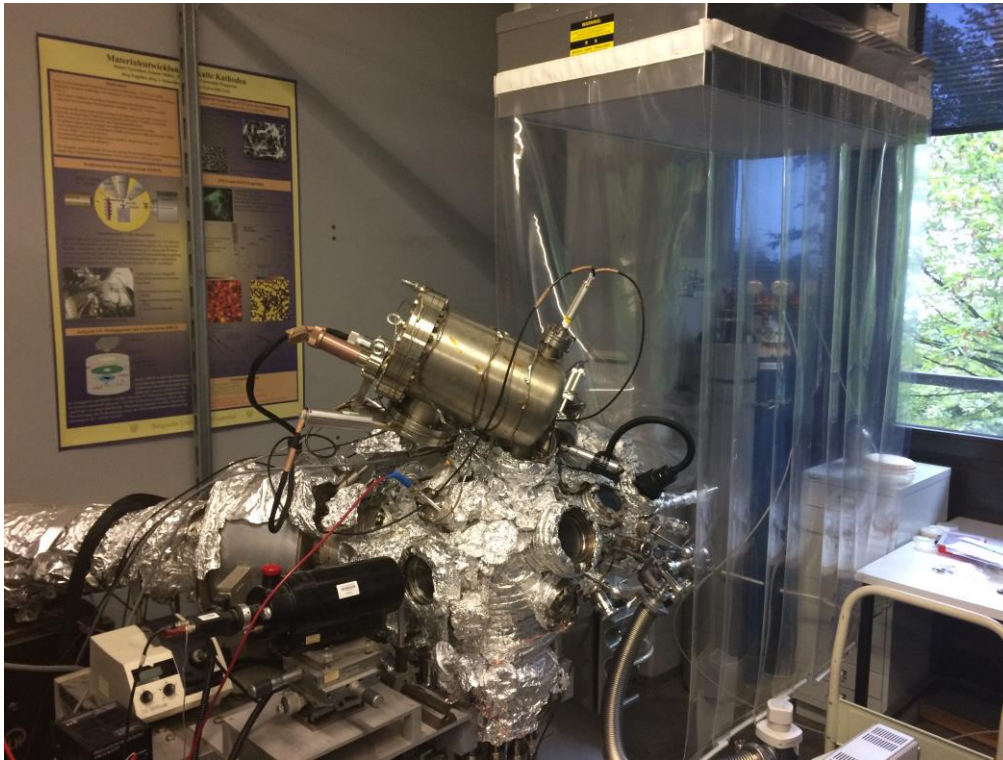
Stronger if $r_p < d_{ox}$

$$\beta_p^{on} \approx h_s / r_p$$

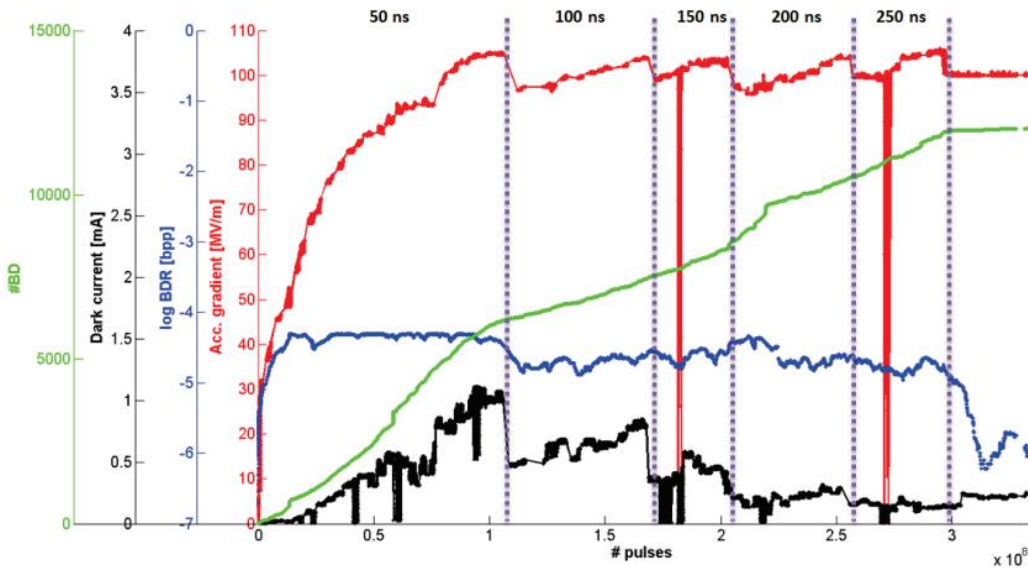


Avoiding particulate contaminations

- A cleanroom environment (class ISO 3) was installed around the load-lock of the FESM to avoid particulate contaminations during installation of samples
- Protection cap mechanically fixed until sample reaches cleanroom environment
- Protection cap loosened under laminar air flow
- Final removal of cap in preparation chamber at $p \sim 10^{-7}$ mbar



Consequences of EFE-results for structure conditioning



- $E_{\text{peak}}/E_{\text{acc}} = 2.43$
- After 1,800 h ~12,000 BDs in 28 cells → ~430 BDs per cell [2]
- BD rate still too high (factor 10)
- **Goal: BD rate < 10^{-7} BD/pulse/m**
- EFE reduced but still present

- Actual cleaning: Ultrasonic baths with de-ionized water and clean alcohol
- Potential improvements due to EFE results:
 - N_2 -cleaning → factor 1.8 – 2.8 → BD rate still too high
 - DIC → factor 7.7 – 12.3 → **goal for BD rate achievable**
- Conditioning results of a N_2 /DIC-cleaned accel. structure still pending

[2] A. Degiovanni et al., WEPME015, Proc. IPAC2014, <http://jacow.org/>.

Cleaning process

- Cleaning of (grounded) samples with handgun (d ~ 5 cm) typically for 5 min
- Liquid CO₂ (10 bar) and N₂ (8 - 10 bar, propellant gas)
→ Flat (12x3 mm) or round (Ø = 5 - 10 mm) jet of CO₂ snow particles
- Samples are treated 2.5 min under 90° / 45° and 3 x rotated in 90° steps
- Teflon protection caps are cleaned as well

